

New Jersey Semi-Conductor Products, Inc.

20 STERN AVE.
SPRINGFIELD, NEW JERSEY 07081
U.S.A.

MJE240 THRU MJE244 NPN
MJE250 THRU MJE254 PNP

TELEPHONE: (973) 376-2922
(212) 227-6005
FAX: (973) 376-8960

COMPLEMENTARY SILICON POWER TRANSISTORS

JEDEC TO-126 GASE

MJE240, MJE250 series types are complementary silicon power transistors designed for audio amplifier and switching applications.

MAXIMUM RATINGS ($T_A=25^\circ\text{C}$ unless otherwise noted) MJE240, MJE241 MJE243, MJE244
MJE242, MJE250 MJE253, MJE254

	<u>SYMBOL</u>	<u>MJE251, MJE252</u>	<u>UNIT</u>
Collector-Base Voltage	V_{CBO}	80	V
Collector-Emitter Voltage	V_{CEO}	80	V
Emitter-Base Voltage	V_{EBO}	7.0	V
Collector Current	I_C	4.0	A
Collector Current (PEAK)	I_{CM}	8.0	A
Base Current	I_B	1.0	A
Power Dissipation	P_D	1.5	W
Power Dissipation ($T_C=25^\circ C$)	P_D	15	W
Operating and Storage			
Junction Temperature	T_J, T_{STG}	-65 to +150	°C
Thermal Resistance	θ_{JA}	83.4	°C/W
Thermal Resistance	θ_{JC}	8.34	°C/W

ELECTRICAL CHARACTERISTICS ($T_C=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNIT
CBO	V _{CB} =80V, (MJE240, 241, 242, 250, 251, 252)	0.1		μA
CBO	V _{CB} =100V, (MJE243, 244, 253, 254)	0.1		μA
CBO	V _{CB} =80V, T _C =125°C (MJE240, 241, 242, 250, 251, 252)	0.1		mA
CBO	V _{CB} =100V, T _C =125°C (MJE243, 244, 253, 254)	0.1		mA
EBO	V _{BE} =7.0V	0.1		μA
BV _{CEO}	I _C =10mA, (MJE240, 241, 242, 250, 251, 252)	80		V
BV _{CEO}	I _C =10mA, (MJE243, 244, 253, 254)	100		V
V _{CE(SAT)}	I _C =500mA, I _B =50mA	0.3		V
V _{CE(SAT)}	I _C =1.0A, I _B =100mA, (MJE241, 243, 251, 253)	0.6		V
V _{CE(SAT)}	I _C =2.0A, I _B =200mA, (MJE240, 250)	0.8		V
V _{BE(SAT)}	I _C =2.0A, I _B =200mA	1.8		V
V _{BE(ON)}	V _{CE} =1.0V, I _C =500mA	1.5		V
h _{FE}	V _{CE} =1.0V, I _C =200mA, (MJE240, 250)	40	200	
h _{FE}	V _{CE} =1.0V, I _C =200mA, (MJE241, 251)	40	180	
h _{FE}	V _{CE} =1.0V, I _C =200mA, (MJE243, 253)	40	180	
h _{FE}	V _{CE} =1.0V, I _C =200mA, (MJE242, 244, 252, 254)	25	-	
h _{FE}	V _{CE} =1.0V, I _C =1.0A, (MJE241, 251)	20	-	
h _{FE}	V _{CE} =1.0V, I _C =1.0A, (MJE243, 253)	15	-	
h _{FE}	V _{CE} =1.0V, I _C =1.0A, (MJE242, 244, 252, 254)	10	-	
h _{FE}	V _{CE} =1.0V, I _C =2.0A, (MJE240, 250)	15	-	
f _T	V _{CE} =10V, I _C =1.0A, f=1.0MHz	2.0		MHz
C _{ob}	V _{CB} =10V, I _E =0, f=0.1MHz, (NPN types)	50		pF
C _{ob}	V _{CB} =10V, I _E =0, f=0.1MHz, (PNP types)	70		pF



NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.